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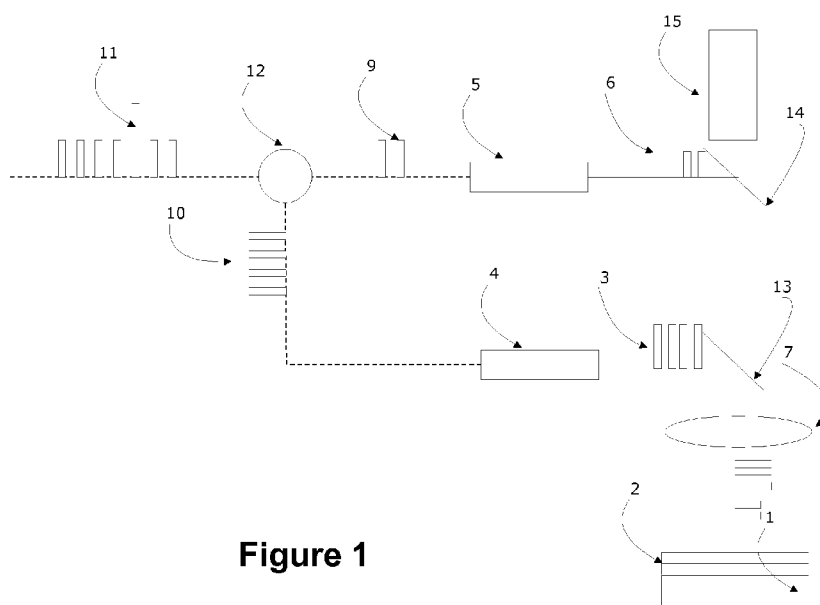


Figure 1

(57) Abstract: A method and apparatus for machining, or forming a feature in, a patterned silicon wafer includes removing portions of surface layers on the wafer using a first pulsed laser (4) beam with a pulse width between 1ps and 1000ps; and removing portions of bulk silicon (1) underlying the surface layers from the wafer using a second pulsed laser (5) beam with a wavelength between 200nm and 1100nm. Re-deposited silicon may be removed from the wafer by etching.

